

09/660,386

PATENT

AMENDMENT IN RESPONSE TO  
(OFFICE ACTION DATED DECEMBER 27, 2002)

FI  
D2  
cont  
a second well of the second conductivity type formed in the semiconductor material, the second well being spaced apart from the first well by a gap and having a dopant concentration;

a third contact region of the first conductivity type formed in the second well;  
a fourth contact region of the second conductivity type formed in the second well, the fourth contact region being electrically connected to the third contact region to have a same potential; and

a second trigger region of the second conductivity type formed in the second well, the second trigger region being spaced apart from the third and fourth contact regions, the first trigger region being positioned such that no other region having the second conductivity type lies between the first trigger region and the second trigger region.

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Please add the following new claims:

--16. A device formed in a semiconductor material of a first conductivity type, the device comprising:

FI  
D2  
cont  
a first well of a second conductivity type formed in the semiconductor material, the first well having a dopant concentration;

a second well of the second conductivity type formed in the semiconductor material, the second well having a dopant concentration and being spaced apart from the first well;

a gap region of the semiconductor material located only between the first and second wells;

a first contact region of the first conductivity type formed in the first well;

a second contact region of the second conductivity type formed in the first well, the second contact region being electrically connected to the first contact region to have a same potential;

09/660,386

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a first trigger region of the second conductivity type formed in the first well, the first trigger region being spaced apart from the first and second contact regions and contacting the gap;

a third contact region of the first conductivity type formed in the second well;

a fourth contact region of the second conductivity type formed in the second well, the fourth contact region being electrically connected to the third contact region to have a same potential;

a second trigger region of the second conductivity type formed in the second well, the second trigger region being spaced apart from the third and fourth contact regions and contacting the gap.

17. The device of claim 16 wherein the first and second trigger regions are formed on opposite sides of the gap.

18. The device of claim 16 wherein the first trigger region has a dopant concentration greater than the dopant concentration of the first well; and

the second trigger region has a dopant concentration greater than the dopant concentration of the second well.

19. The device of claim 16 wherein the first trigger region is positioned such that no other region similar to the first trigger region and the second trigger region lies between the first trigger region and the second trigger region

20. The device of claim 16 wherein the first trigger region is not electrically connected to the third contact region to have a same potential, and the second trigger region is not electrically connected to the first contact region to have a same potential.

09/660,386

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21. The device of claim 8 wherein no other region having the second conductivity type and a dopant concentration greater than the first well lies between the first trigger region and the second trigger region.--

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